## AMENDMENTS TO THE CLAIMS

Claim 1. (Currently Amended) An SPST (single-pole single-throw) switch for controlling propagation of a high frequency signal between an input terminal and an output terminal, said SPST switch comprising:

a plurality of first-field-effect transistor (FET) switches connected in parallel, each of <u>said</u> plurality of FET switches having which includes a field-effect transistor having its <u>awhose</u> drain and source <u>are directly</u> connected in parallel with an inductor, wherein

the input of said plurality of FET switches is directly connected to the input terminal of said SPST switch and the output of said plurality of FET switches is directly connected to the output terminal of said SPST switch;

each of said field-effect transistors has-its-an ON state and an OFF state changed by a voltage applied to a gate of each of said field-effect transistors, and

each of said field-effect transistors has-its- an OFF capacitance that causes eause parallel resonance with said inductor connected at a frequency of the high frequency signal.

Claims 2-3. (Canceled)

Claim 4. (Currently Amended) An SPST (single-pole single-throw) switch for controlling propagation of a high frequency signal between an input terminal and an output terminal, said SPST switch comprising:

a second-field-effect transistor (FET) switch constructed by <u>directly</u> connecting an inductor in parallel with a series circuit, <u>the series circuit consisting</u> of <u>a capacitor connected in series with a drain or source of and a FET field-effect transistor that has its drain or source connected in series with the capacitor, wherein</u>

said field-effect transistor<u>FET</u> has its an ON state and <u>an OFF</u> state changed by a voltage applied to a gate of said field-effect transistor<u>FET</u>, and

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said field-effect transistor FET has its a parasitic inductor and said capacitor that cause series resonance, and has its an OFF capacitance which causes eause parallel resonance with said inductor.

Claim 5. (Currently Amended) The SPST switch according to claim 4, wherein the input of said second field-effect transistor FET switch is directly connected betweento the input terminal of said SPST switch and the output of said FET switch is directly connected to the output terminal of said SPST switch.

Claim 6. (Currently Amended) The SPST switch according to claim 5, whereinfurther comprising a plurality of second field-effect transistor FET switches are connected in parallel between the input terminal and the output terminal.

Claim 7. (Currently Amended) The SPST switch according to claim 4, wherein the input of said FET switch is directly connected to the input terminal of said SPST-are connected to each other; and

the output of said <u>FET</u>second field-effect transistor switch is <u>directly</u> connected between the input terminal and ato ground.

Claim 8. (Currently Amended) The SPST switch according to claim 7, whereinfurther comprising

a plurality of second field-effect transistor FET switches are connected in parallel, wherein the input of said plurality of parallel FET switches is directly connected to between the input terminal of said SPST and the output of said plurality of parallel FET switches is directly connected to ground.

Claim 9. (Currently Amended) An SPDT (single-pole double-throw) switch for controlling propagation of a high frequency signal between an input terminal and two output terminals, said SPDT switch employing:

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a plurality of <u>first-field-effect</u> transistor <u>(FET)</u> switches as <u>defined in claim 1</u>, <u>which are</u> connected in parallel, <u>each of said plurality of FET switches having a field-effect transistor</u> <u>whose drain and source are directly connected in parallel with an inductor; and</u>

wherein the input of said plurality of parallel FET switches is directly connected to the input terminal of said SPDT switch and the output of said plurality of parallel FET switches is directly connected to a first output terminal of said SPST switch.

Claim 10. (Currently Amended) AnThe SPDT (single-pole double-throw) switch of claim 9, for controlling propagation of a high frequency signal between an input terminal and two output terminals, said SPDT switch employing further comprising:

a second single field-effect transistor (FET) switch as defined in claim 4 having an inductor directly connected in parallel with a series circuit, the series circuit consisting of a capacitor connected in series with a drain or source of a field-effect transistor; and

wherein the input of said single FET switch is directly connected to a second output terminal of said SPST switch and the output of said single FET switch is directly connected to ground.

Claim 11. (Currently Amended) An MPMT (multiple-pole multiple throw) switch for controlling propagation of a high frequency signal between a plurality of input terminals and a plurality of output terminals, said MPMT switch employing:

a plurality of first-field-effect transistor (FET) switches as defined in claim 1, which are connected in parallel, each of said plurality of parallel FET switches having a field-effect transistor whose drain and source are directly connected in parallel with an inductor; and

wherein the input of said plurality of parallel FET switches is directly connected to an input terminal of said MPDT switch and the output of said plurality of parallel FET switches is directly connected to an output terminal of said SPST switch.

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Claim 12. (Currently Amended) An MPMT (multiple-pole multiple throw) switch for controlling propagation of a high frequency signal between a plurality of input terminals and a plurality of output terminals, said MPMT switch employing:

<u>a plurality of second-field-effect transistor (FET)</u> switches, each of said FET switches <u>having an inductor directly connected in parallel with a series circuit, the series circuit consisting</u> <u>of a capacitor connected in series with a drain or source of a field-effect transistor as defined in claim 4.</u>

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